

ABSTRACT

A highly durable mask with sufficient strength against ion implantation, a method of producing the same, 5 and a method of producing a semiconductor device using the mask are provided. A mask comprising a thin film, a protective film preferably composed of a photosensitive resin formed on a part of the thin film, a supporting frame formed on the thin film to surround the protective 10 film, and holes formed in the thin film and the protective film for allowing a charged particle beam or a electromagnetic wave irradiated on the protective film side to pass; the method of producing the same; and a method of producing a semiconductor device including an 15 ion implantation step using the same.